sapcon®

SR102 - SR1100

1.0A SCHOTTKY BARRIER DIODE

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

Mechanical Data

- Case: DO-41, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Lead Free: For RoHS / Lead Free Version,

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SR102	SR104	SR106	SR1100	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	20	40	60	100	V
RMS Reverse Voltage	VR(RMS)	14	28	42	70	V
Average Rectified Output Current $@T_L = 100^{\circ}C$ (Note 1)	lo	1.0			А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	40			A	
Forward Voltage @I _F = 1.0A	Vfm		0.5	0.7	0.85	V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	Iгм	0.5 10			mA	
Typical Junction Capacitance (Note 2)	Cj	110 80		pF		
Typical Thermal Resistance (Note 1)	R∂JL R∂JA	15 50		°C/W		
Operating and Storage Temperature Range	Тj, Tsтg	-65 to +150		°C		

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.



DO-41					
Dim	Min	Max			
Α	25.4	—			
В	4.06	5.21			
С	0.71	0.864			
D	2.00	2.72			
All Dimensions in mm					

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